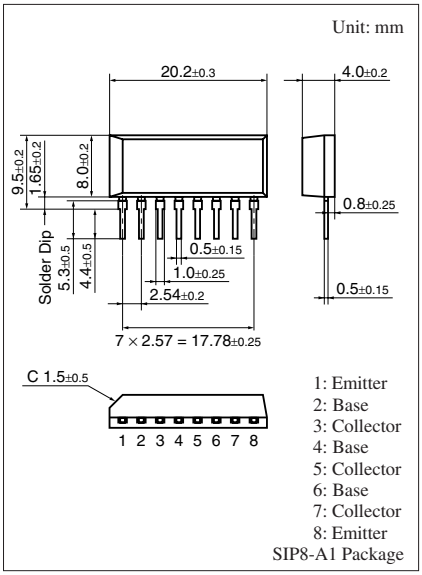
PUA3110 (PU3110)

Silicon NPN triple diffusion planar type

For power amplification/switching
Complementary to PUA3210 (PU3210)



■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- NPN 3 elements

■ Absolute Maximum Ratings $T_C = 25°C$

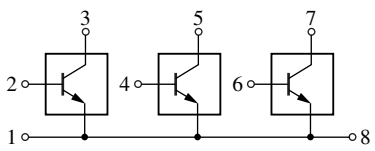
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	60	V
Collector-emitter voltage (Base open)	V_{CEO}	60	V
Emitter-base voltage (Collector open)	V_{EBO}	6	V
Collector current	I_C	3	A
Peak collector current	I_{CP}	5	A
Base current	I_B	1	A
Collector power dissipation	P_C	15	W
$T_a = 25°C$		2.4	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

■ Electrical Characteristics $T_C = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	I_C = 30 mA, I_B = 0	60			V
Base-emitter voltage	V_{BE}	V_{CE} = 4 V, I_C = 3 A			1.8	V
Collector-emitter current (E-B short)	I_{CES}	V_{CE} = 60 V, V_{BE} = 0			200	µA
Collector-emitter cutoff current (Base open)	I_{CEO}	V_{CE} = 30 V, I_B = 0			300	µA
Emitter-base cutoff current (Collector open)	I_{EBO}	V_{EB} = 6 V, I_C = 0			1	mA
Forward current transfer ratio	h_{FE1}	V_{CE} = 4 V, I_C = 1 A	70		250	—
	h_{FE2}	V_{CE} = 4 V, I_C = 3 A	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 3 A, I_B = 0.375 A			1.2	V
Transition frequency	f_T	V_{CE} = 10 V, I_C = 0.5 A, f = 10 MHz		30		MHz
Turn-on time	t_{on}	I_C = 1 A		0.5		µs
Storage time	t_{stg}	I_{B1} = 0.1 A, I_{B2} = − 0.1 A		2.5		µs
Fall time	t_f	V_{CC} = 50 V		0.4		µs

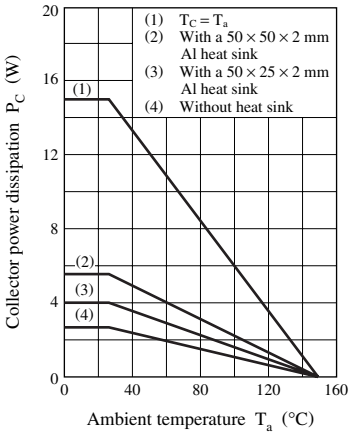
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

■ Internal Connection

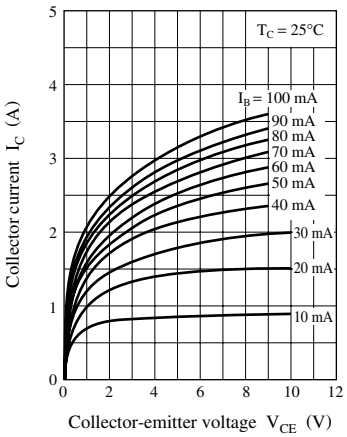


Note) The part number in the parenthesis shows conventional part number.

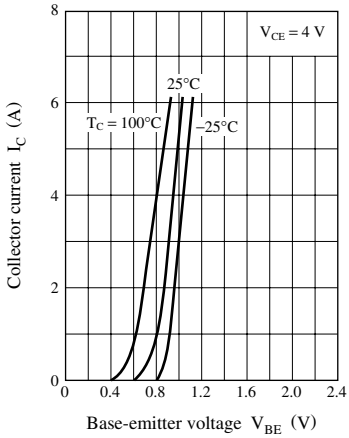
P_C — T_a



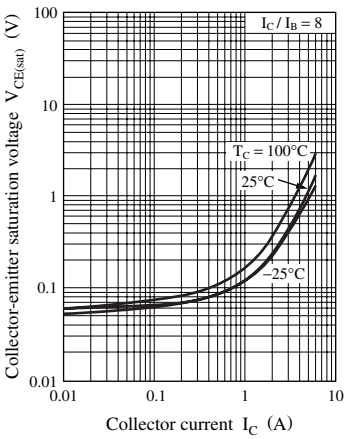
I_C — V_{CE}



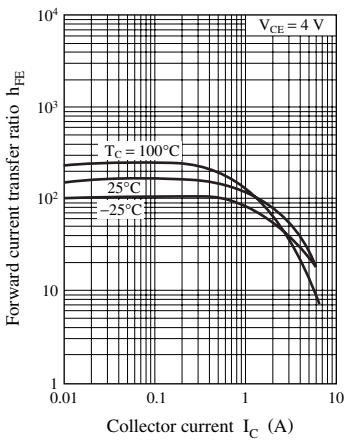
I_C — V_{BE}



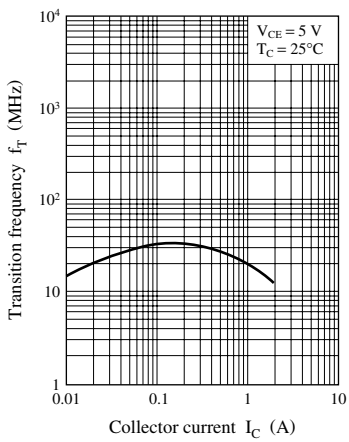
$V_{CE(sat)}$ — I_C



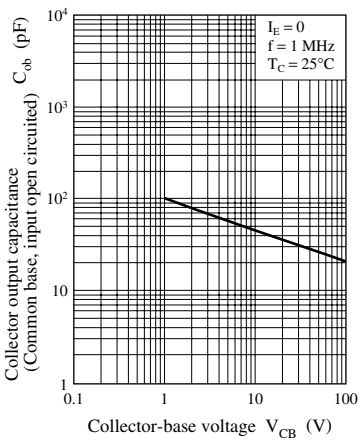
h_{FE} — I_C



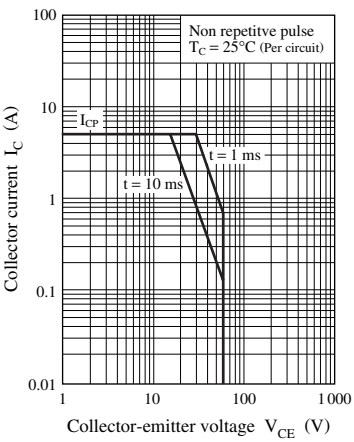
f_T — I_C



C_{ob} — V_{CB}



Safe operation area



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